

## SOT-23 Plastic-Encapsulate Transistors

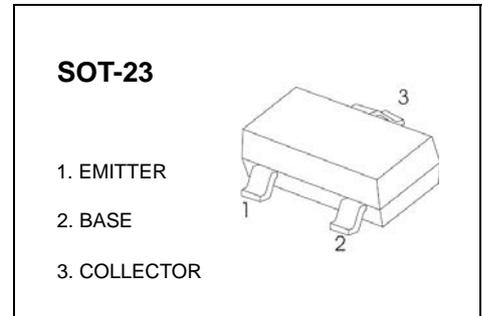
TRANSISTOR (NPN)

### FEATURES

Complimentary to S8550

Collector Current:  $I_C=0.5A$

MARKING: J3YN

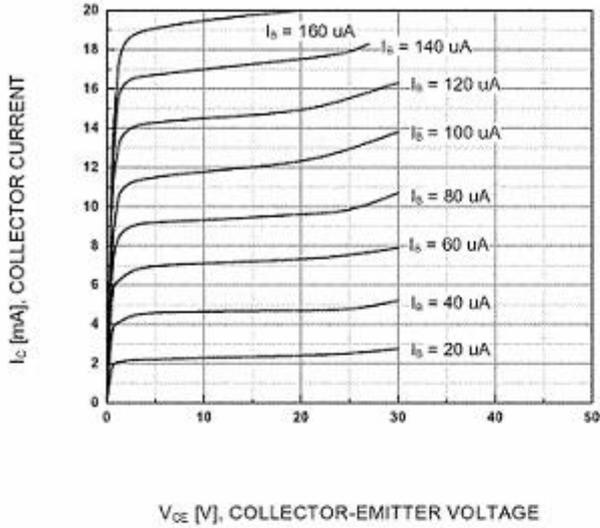
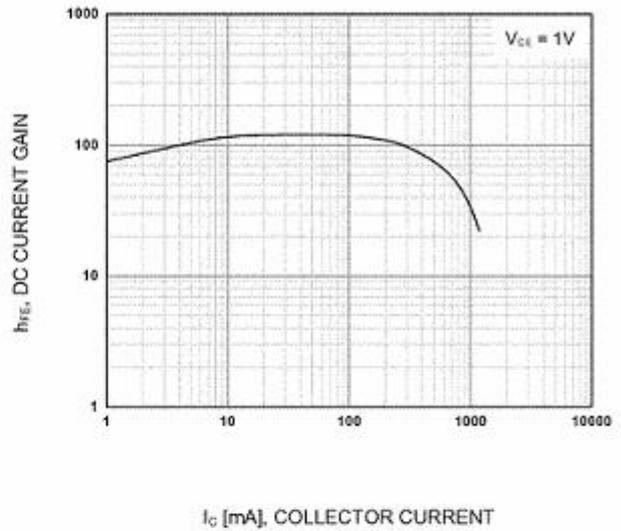
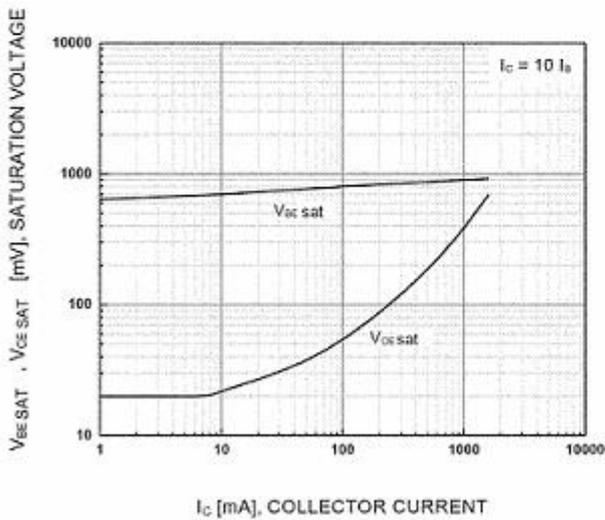
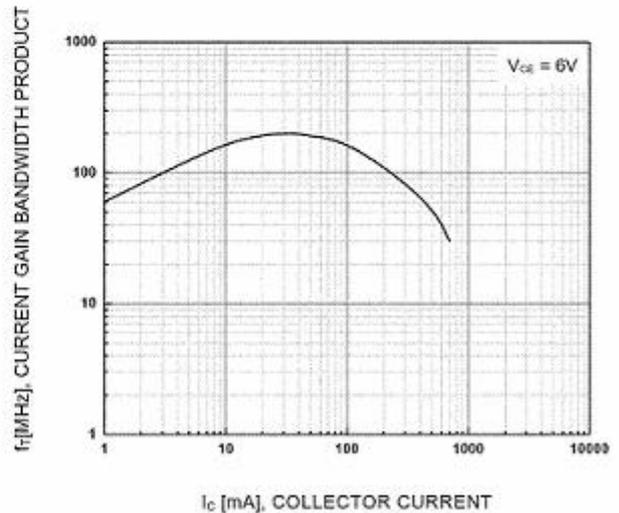


### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	40	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	0.5	A
$P_C$	Collector Dissipation	0.3	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$ , $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40\text{V}$ , $I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CB}=20\text{V}$ , $I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}$ , $I_C=0$			0.1	$\mu\text{A}$
DC current gain	$H_{FE(1)}$	$V_{CE}=1\text{V}$ , $I_C=50\text{mA}$	200		350	
	$H_{FE(2)}$	$V_{CE}=1\text{V}$ , $I_C=500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$ , $I_B=50\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}$ , $I_B=50\text{mA}$			1.2	V
Transition frequency	$f_T$	$V_{CE}=6\text{V}$ , $I_C=20\text{mA}$ $f=30\text{MHz}$	150			MHz

**Typical Characteristics**

**Static Characteristic**

**DC current Gain**

**Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**

**Current Gain Bandwidth Product**